

SB5560S 55A SCR

FEATURES

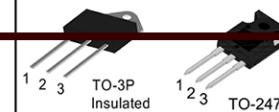
- High thermal cycling performance
- High voltage capacity
- Very high current surge capability

APPLICATIONS

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

Parameters Summary

VD/VR:1200/1600V IT(RMS):55A IGT :60mA

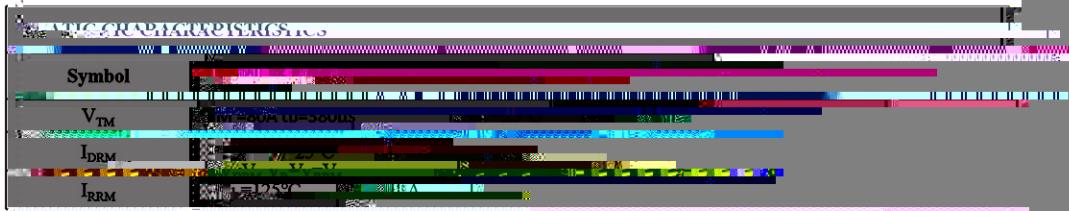


ABSOLUTE MAXIMUM RATINGS

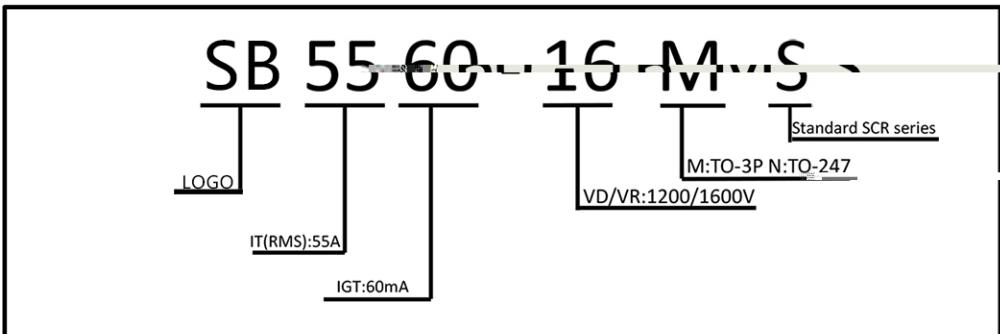
Parameter	Symbol	value	Unit
Storage junction temperature range	T _{stg}	-40 ~ 150	°C
Operating junction temperature range	T _j	-40 ~ 125	°C
Repetitive peak off-state voltage (T=25°C)	V _{DRM}	1200/1600	V
Repetitive peak reverse voltage (T=25°C)	V _{RPM}	1200/1600	V
Non repetitive surge peak Off-state voltage	V _{DSM}	V _{DRM} +100	V
Non repetitive peak reverse voltage	V _{RSM}	V _{RPM} +100	V
RMS on-state current	I _{T(80°C)}	55	A
	I _{T(85°C)}	55	A
Non repetitive surge peak on-state current	I _{TSM}	550	A
Average on-state current (180° conduction angle)	I _{T(AV)}	35	A
I ² t value for fusing (tp=10ms)	I ² t	1500	A ² S
Critical rate of rise of on-state current (I=2×IGT, tr ≤ 100 ns)	di/dt	150	A/μS
Peak gate current	I _{GM}	5	A
Average gate power dissipation	P _{G(AV)}	2	W

Thermal Resistances

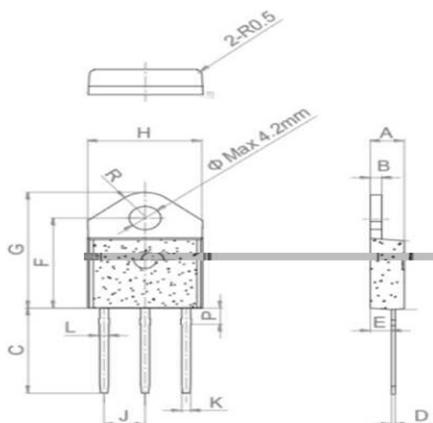
Symbol	Parameter	Value	Unit
R _{th(j-c)}	Junction to case (DC)	TO-3P	0.65
		TO-247	0.60
			°C/W



Ordering Information Scheme

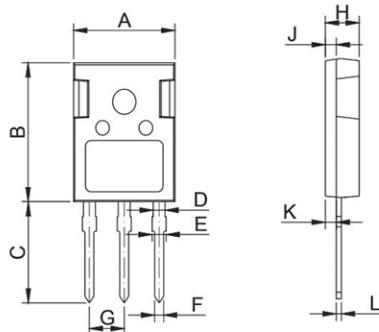


TO-3P Package Mechanical Data



Ref.	Parameters	Dimensions
A	Height	4.00
B	Lead thickness	0.60
C	Lead spacing	1.00
D	Lead pitch	1.90
E	Lead width	1.00
F	Lead thickness	0.10
G	Lead height	1.00
H	Lead width	1.00
I	Lead thickness	0.10
J	Lead height	1.00
K	Lead width	1.00
L	Lead thickness	0.10
P	Lead thickness	0.10
R	Lead thickness	0.10

TO-247 Package Mechanical Data



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	15.50	15.80	15.90	0.610	0.622	0.634
B	20.80	21.00	22.20	0.810	0.828	0.874
C	19.70	20.00	20.30	0.776	0.787	0.799
D	1.80	2.00	2.00	0.071	0.079	0.081
E	1.90	2.10	2.30	0.075	0.083	0.091
F	1.00	1.20	1.40	0.039	0.047	0.055
G	5.44	5.50	5.70	0.214	0.217	0.225
H	4.80	5.00	5.20	0.190	0.197	0.205
J	1.90	2.00	2.10	0.075	0.079	0.083
K	2.20	2.35	2.50	0.087	0.093	0.098
L	0.41	0.60	0.79	0.016	0.024	0.031

FIG.1 Maximum power dissipation versus on-state current

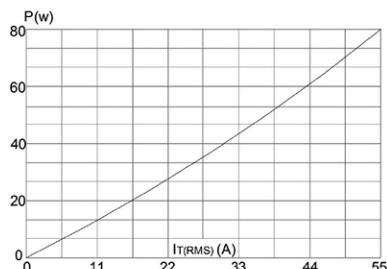


FIG.3: Surge peak on-state current versus number of cycles

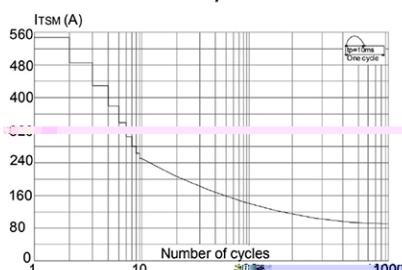


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width, $t_p < 10\text{ms}$, and corresponding value of $I_2 t$

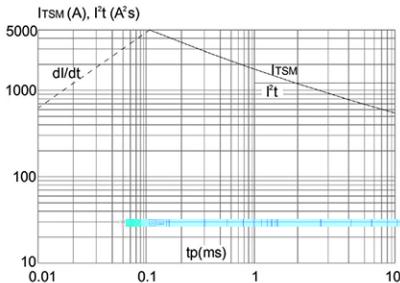


FIG.2: on-state current versus case temperature

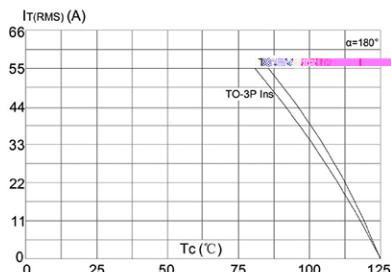


FIG.4: On-state characteristics (maximum values)

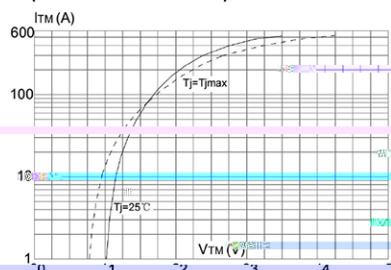


FIG.6: Relative variations of gate-to-drain current, drain current, latching current and latching current versus junction temperature

